

# Si-Fototransistoren

Typ	Verlustleistung $P_{\text{tot}}$ (mW)	Kollektor-Emitter-Spannung $U_{\text{CE}}$ (V)	Emitter-Kollektor-Spannung $U_{\text{EC}}$ (V)	Betriebs-temperaturbereich $T_{\text{a}}$ (°C)	Betriebsstrom $I_{\text{C}1}$ (mA)	spektraler Empfindlichkeitsbereich $\lambda_{\text{S}}$ (nm)	Anstiegs- und Abfallzeit $t_{\text{r}}; t_{\text{f}}^{2)}$ (µs)	Bauform
SP 211	50 <sup>3)</sup>	≤ 50	≤ 7	-65 ... 125	0,25 ... 3,2	800 ... 900	≤ 10	49
SP 212 <sup>5)</sup>	100 <sup>4)</sup>	≤ 50	≤ 7	-40 ... 85	0,63 ... ≥ 2,5	800 ... 900	C,D ≤ 10 E,F ≤ 20	63
SP 213	100 <sup>4)</sup>	≤ 50	≤ 7	-40 ... 85	1,0 ... ≥ 4,0	800 ... 900	D,E ≤ 10 F,G ≤ 20	61
SP 215	100 <sup>4)</sup>	≤ 50	≤ 7	-40 ... 85	1,6 ... ≥ 6,3	800 ... 900	E,F ≤ 10 G,H ≤ 20	50

1) bei  $U_{\text{CE}} = 5 \text{ V}; E_{\text{v}} = 1 \text{ kLx}$

2) bei  $U_{\text{B}} = 35 \text{ V}; I_{\text{C}} = 800 \text{ µA}$

3)  $T_{\text{a}} = -65 \dots 25 \text{ °C}$

4)  $T_{\text{a}} = -40 \dots 25 \text{ °C}$

5) abweichende Gruppen

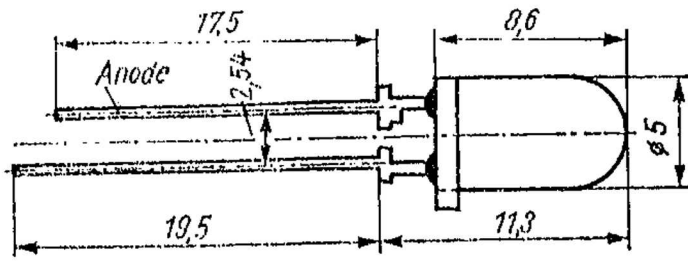


Bild 45

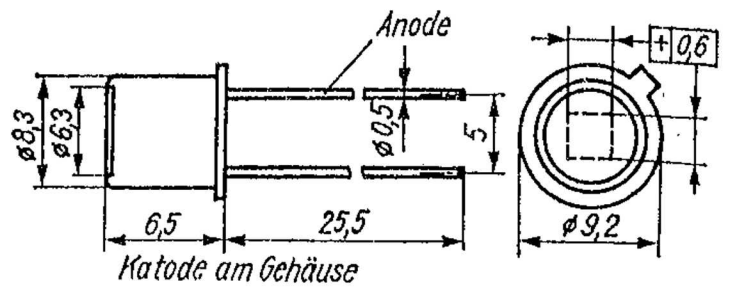


Bild 46

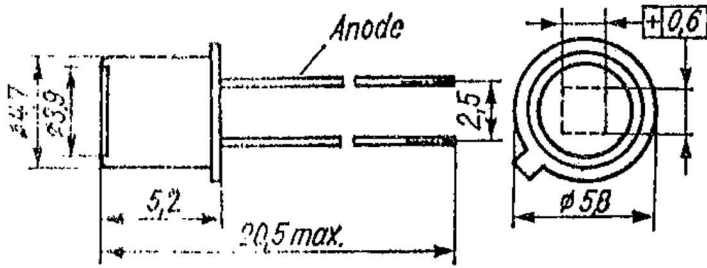


Bild 47

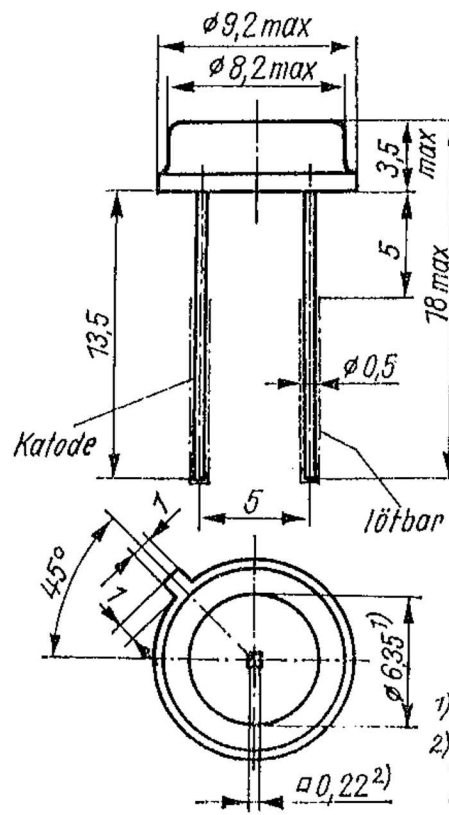


Bild 48

1) Lichteintrittsöffnung  
2) bestrahlungsempfindliche Fläche

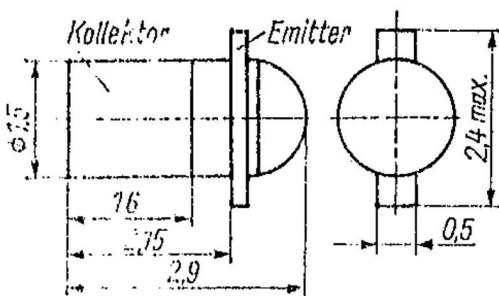


Bild 49

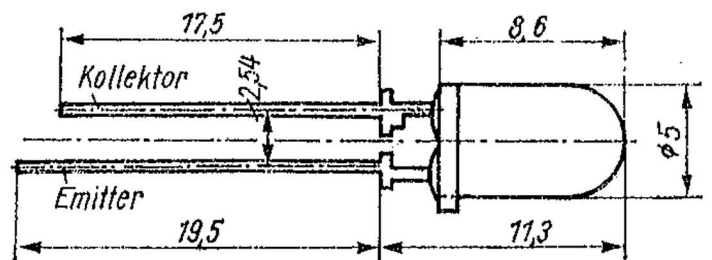


Bild 50

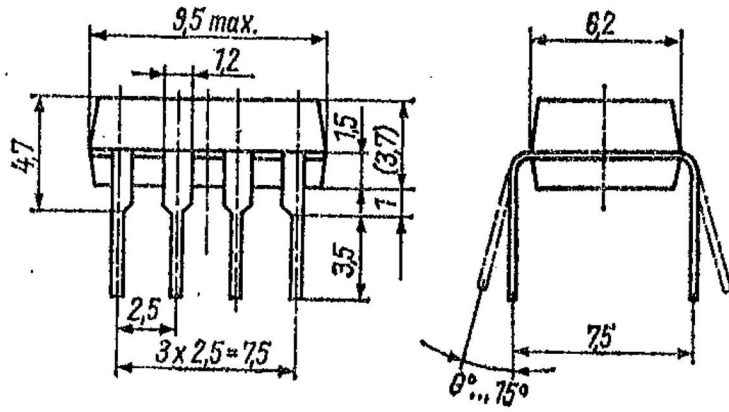


Bild 60

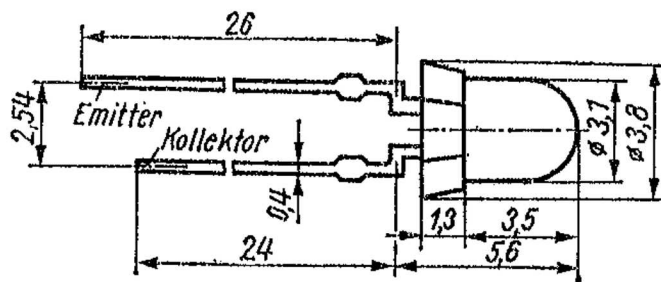


Bild 61

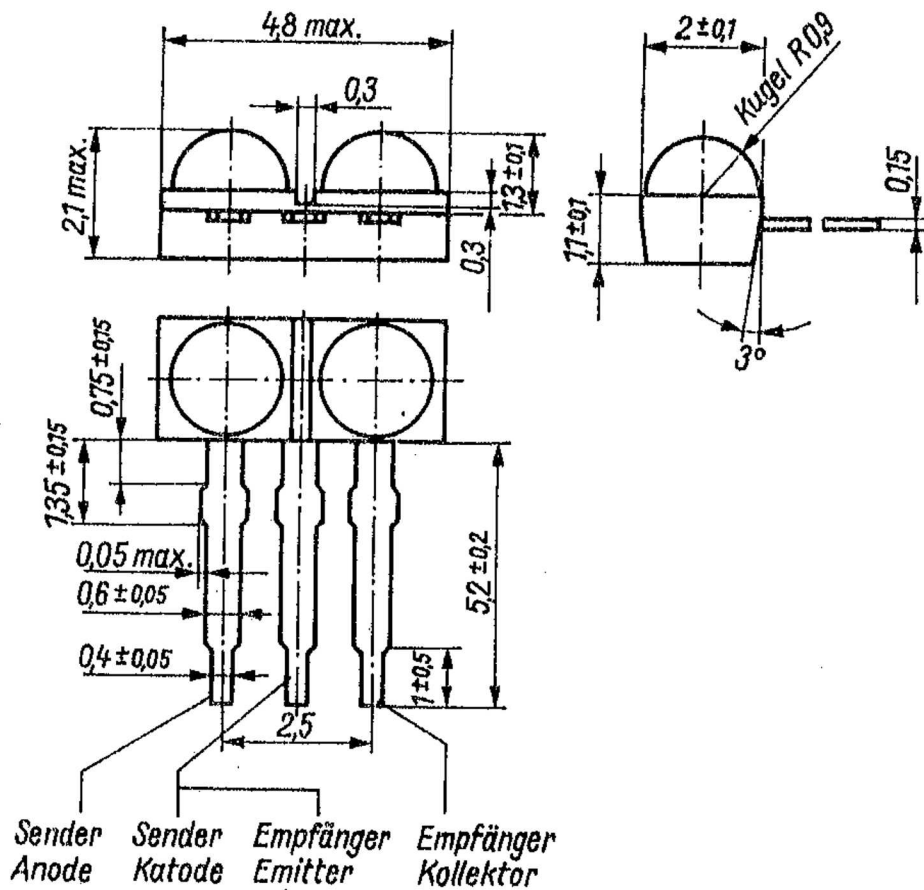


Bild 62

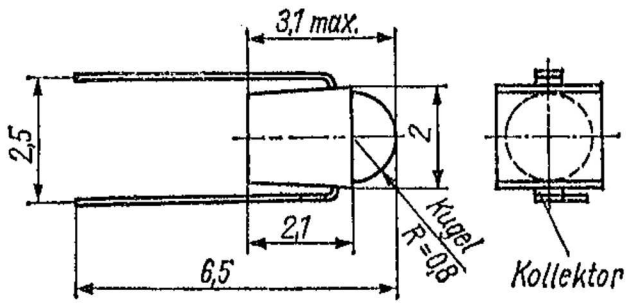


Bild 63

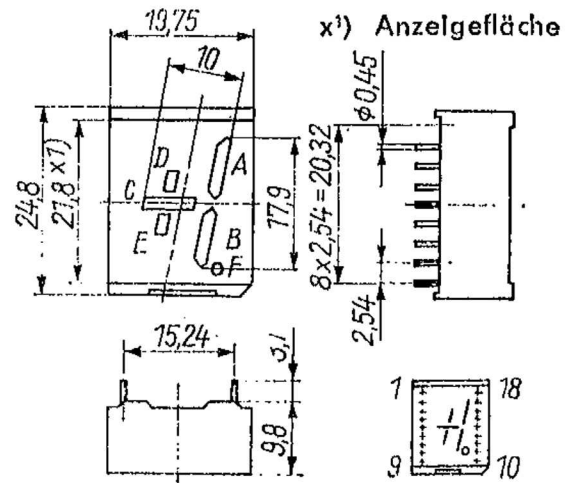
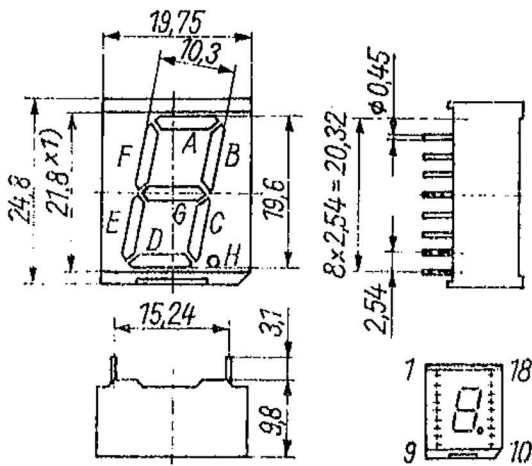


Bild 64



x<sup>1)</sup> Anzeigefläche

Bild 65

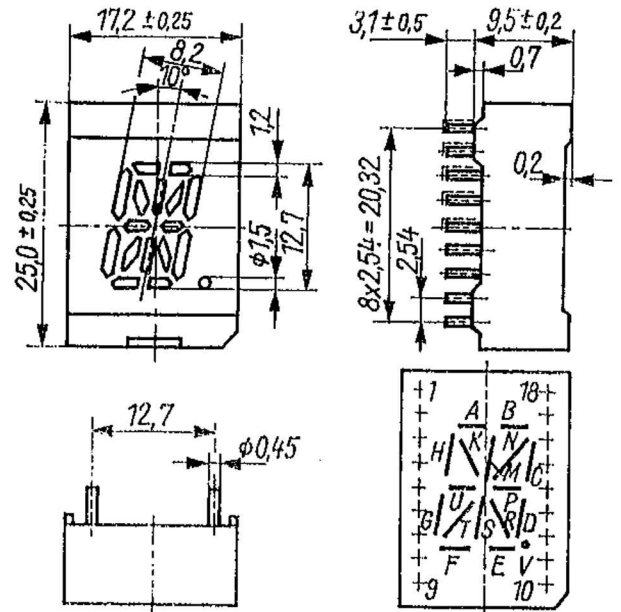
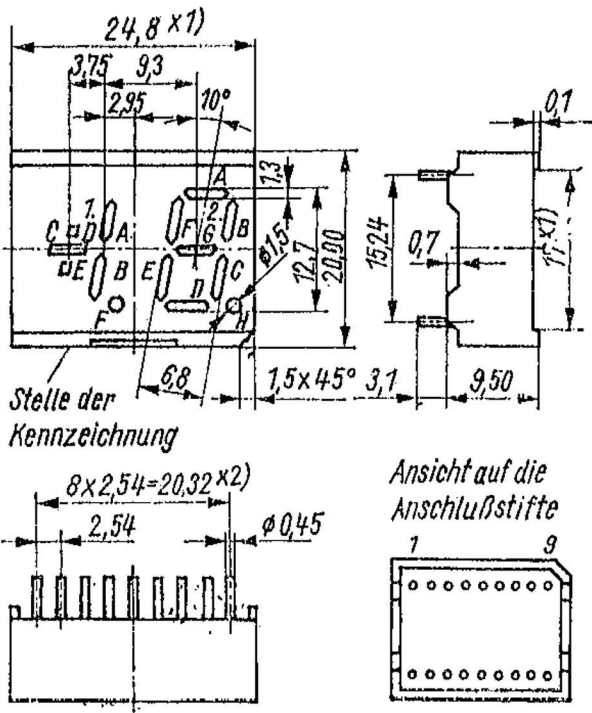
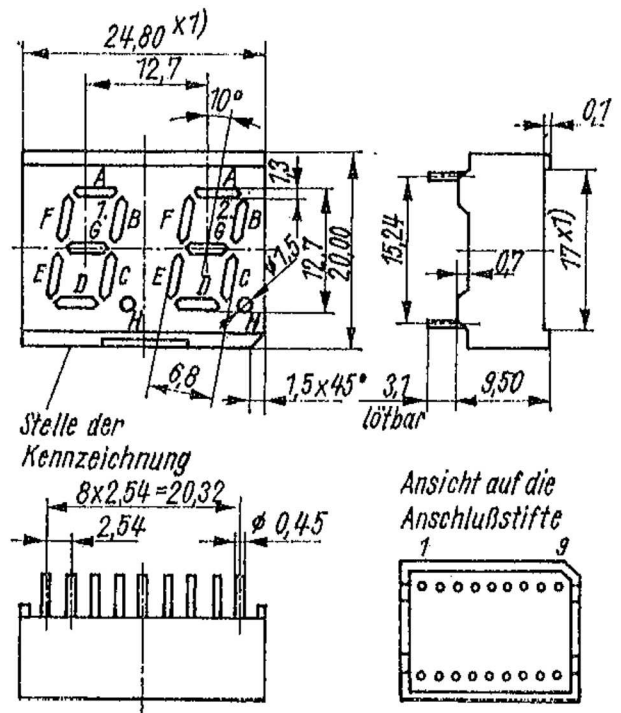


Bild 66



x<sup>1)</sup> Anzeigefläche

Bild 67



x<sup>1)</sup> Anzeigefläche

Bild 68